applied surface science

A journal devoted to the properties of interfaces in relation to the synthesis and behaviour of materials



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A JOURNAL DEVOTED TO THE PROPERTIES OF INTERFACES IN RELATION TO THE SYNTHESIS AND BEHAVIOUR OF MATERIALS

Editors:

L.C. Feldman, Murray Hill, NJ, USA W.F. van der Weg, Utrecht, The Netherlands

Master Index to Volumes 31-40



NORTH-HOLLAND

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Adhesion Adsorption

Adsorption isotherms

Alkali metals

Alloys Alumina Aluminium

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Mercury telluride

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Photoelectrochemistry

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Rare earth metals Rare gas atoms Reactive ion etching

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Residual gas Rhenium Rhodium Roughness Ruthenium

Rutherford backscattering

Scandium

Scanning Auger microprobe Scanning Auger microscopy Scanning electron microscopy Scanning tunneling microscopy

Schottky barrier

Schottky barrier photodiodes Secondary electron yield

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Selenium

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Silane Silica Silicides

Silicides Silicon

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Sputtering

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Sulphides Sulphur

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Supported catalysts
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Surface composition

Surface composition analysis

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Ternary compounds Thermal desorption

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Titanium
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Titanium nitride Titanium oxide Titanium selenide

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Zeolites
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Zinc sulphoselenide
Zirconium
Zirconium dioxide
Zirconium oxide

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- [1] C. Nöbl, C. Benndorf and T.E. Madey, Surf. Sci. 157 (1985) 29.
- [2] D.R. Baer and M.T. Thomas, Appl. Surf. Sci. 26 (1986) 150.
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- [5] R.J. Madix, in: The Chemical Physics of Solid Surfaces and Heterogeneous Catalysis, Vol. 4, Eds. D.A. King and D.P. Woodruff (Elsevier, Amsterdam, 1982) p. 1.

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applied surface science

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